

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit	
[MOSFET]				
V_{DSS}	Drain-Source Voltage	20	V	
V_{GSS}	Gate-Source Voltage	± 10		
I_D^*	Continuous Drain Current	3	A	
I_{DM}^*	300 μs Pulsed Drain Current			
I_S^*	Diode Continuous Forward Current	1	A	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55 to 150		
P_D^*	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	0.83	W
		$T_A=100^\circ\text{C}$	0.3	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient	150	$^\circ\text{C/W}$	
[SBD]				
V_{RRM}	Repetitive Peak Reverse Voltage	20	V	
I_{FSM}	Maximum Peak Forward Surge Current	5.5	A	

Note:

*Surface Mounted on 1in² pad area, $t \leq 10\text{sec}$.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	APM2800B			Unit
			Min.	Typ.	Max.	
[MOSFET]						
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu\text{A}$	20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=16V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			1	μA
			30			
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$	0.45	0.6	1	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 10V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^a$	Drain-Source On-state Resistance	$V_{GS}=4.5V, I_{DS}=3A$		50	70	m Ω
		$V_{GS}=2.5V, I_{DS}=1.7A$		90	110	
V_{SD}^a	Diode Forward Voltage	$I_{SD}=0.5A, V_{GS}=0V$		0.7	1.3	V

Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	APM2800B			Unit
			Min.	Typ.	Max.	
[MOSFET]						
Dynamic Characteristics^b						
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=20V,$ Frequency=1.0MHz		255		pF
C_{oss}	Output Capacitance			70		
C_{rss}	Reverse Transfer Capacitance			50		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=10V, R_L=10\Omega,$ $I_{DS}=1A, V_{GEN}=4.5V,$ $R_G=6\Omega$		6	12	ns
T_r	Turn-on Rise Time			5	10	
$t_{d(OFF)}$	Turn-off Delay Time			12	23	
T_f	Turn-off Fall Time			6	12	
Gate Charge Characteristics^b						
Q_g	Total Gate Charge	$V_{DS}=10V, V_{GS}=4.5V,$ $I_{DS}=3A$		5	6.5	nC
Q_{gs}	Gate-Source Charge			0.7		
Q_{gd}	Gate-Drain Charge			0.7		
[SBD]						
V_R	Reverse Voltage	$I_R=0.5mA$	20			V
V_{F1}	Forward Voltage	$I_F=10mA$			0.4	V
V_{F2}		$I_F=500mA$			0.5	V
I_R	Reverse Current	$V_R=15V$			200	μA
C^b	Junction Capacitance	$V_R=10V,$ Frequency=1.0MHz		45		pF

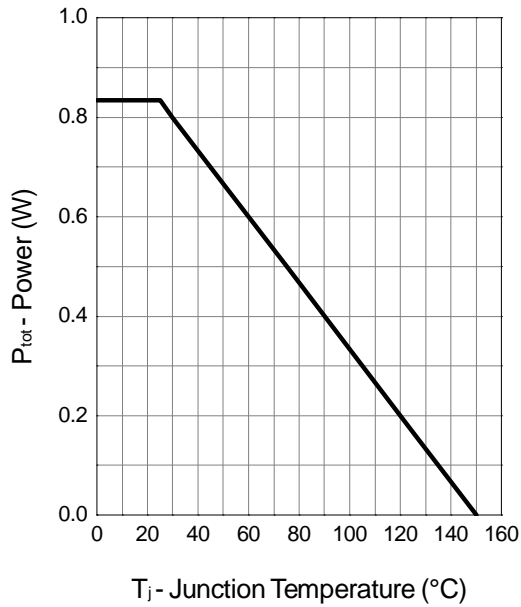
Notes:

- a: Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- b: Guaranteed by design, not subject to production testing

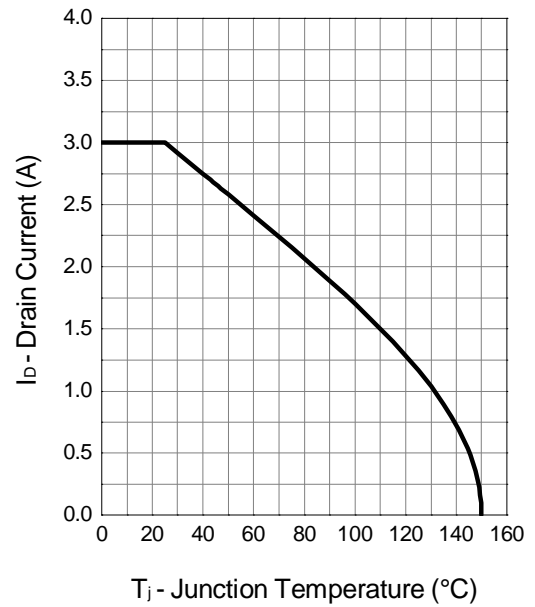
Typical Characteristics

N-Channel MOSFET

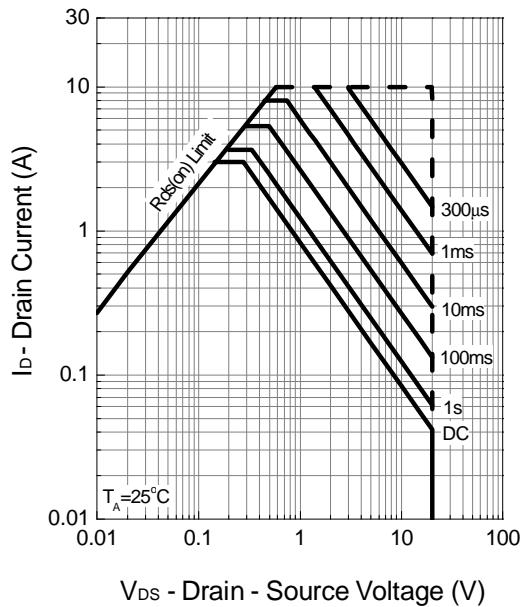
Power Dissipation



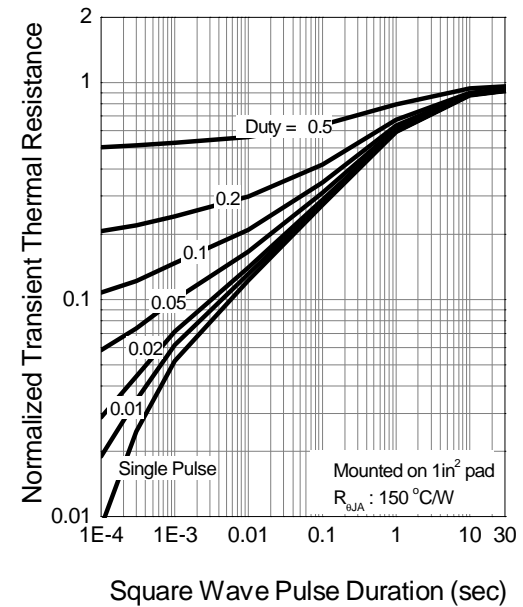
Drain Current



Safe Operation Area

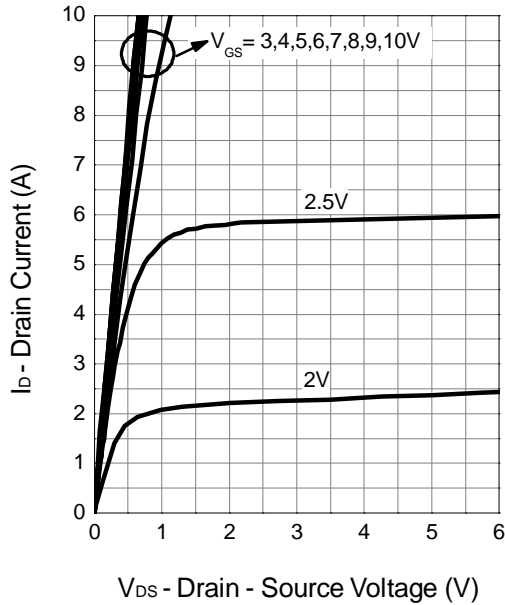


Thermal Transient Impedance

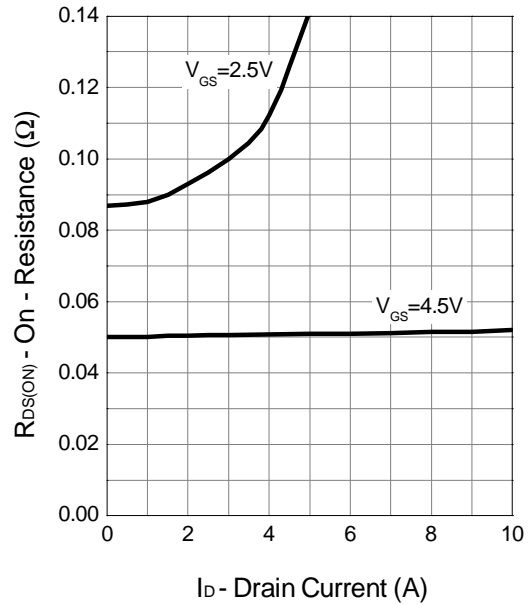


Typical Characteristics (Cont.)

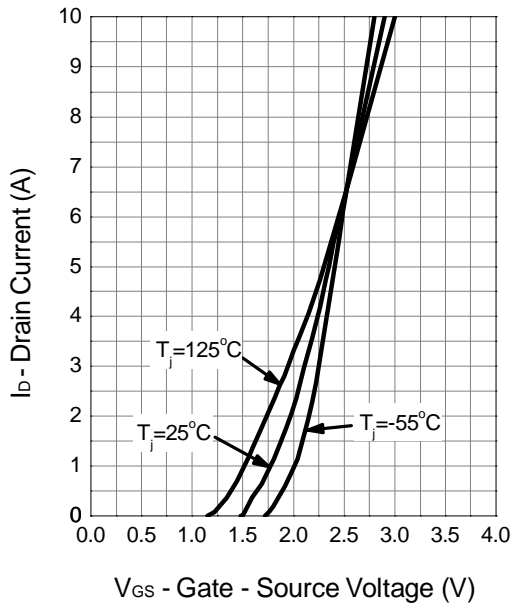
Output Characteristics



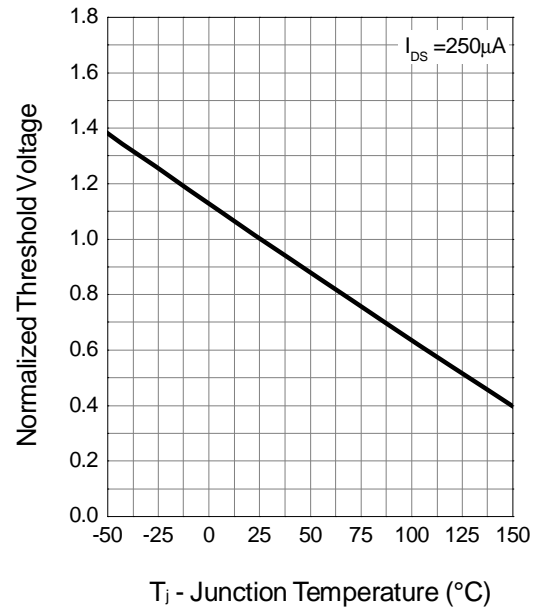
Drain-Source On Resistance



Transfer Characteristics

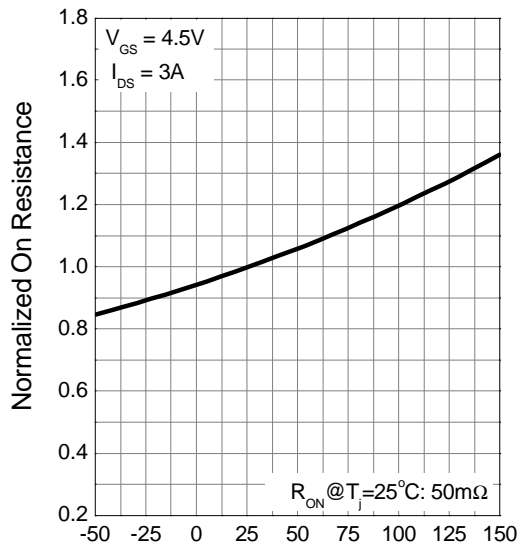


Gate Threshold Voltage



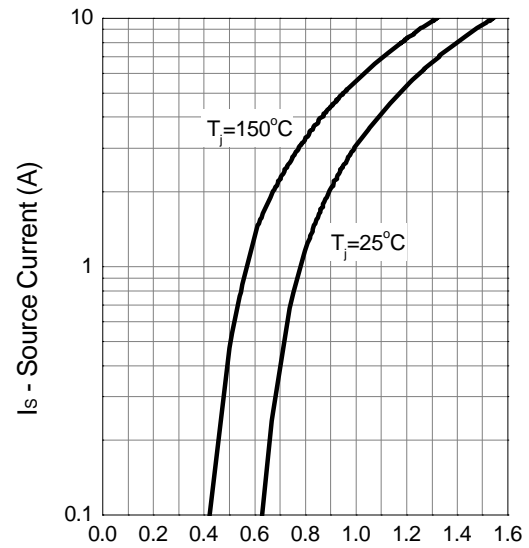
Typical Characteristics (Cont.)

Drain-Source On Resistance



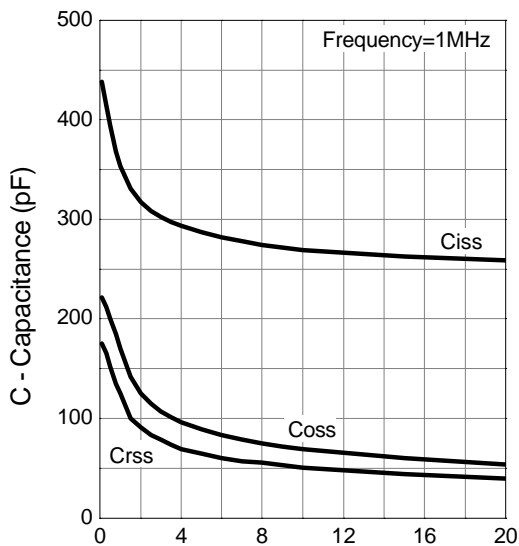
T_j - Junction Temperature (°C)

Source-Drain Diode Forward



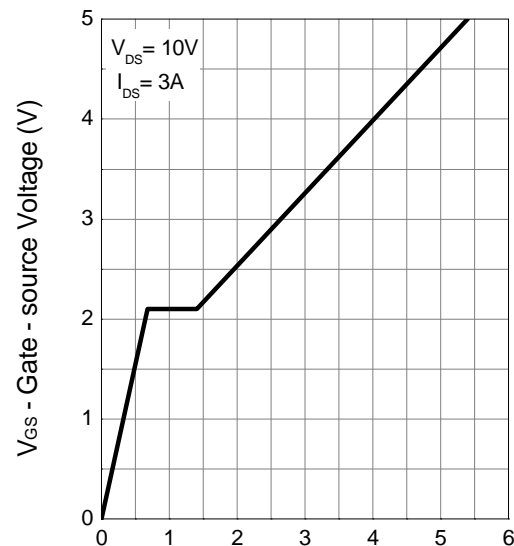
V_{SD} - Source - Drain Voltage (V)

Capacitance



V_{DS} - Drain - Source Voltage (V)

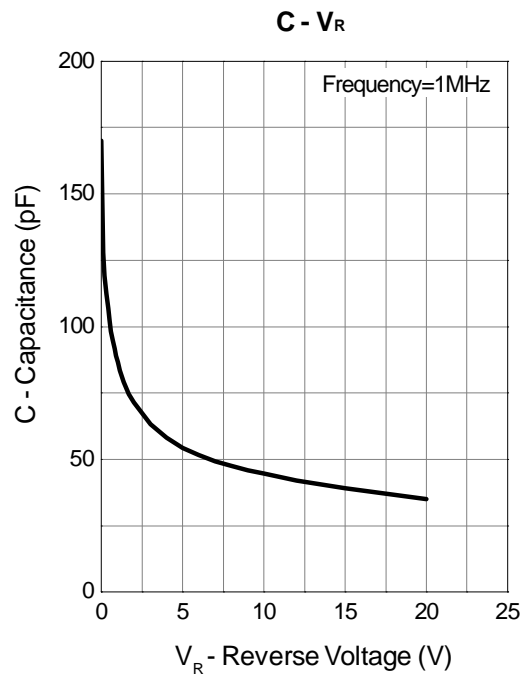
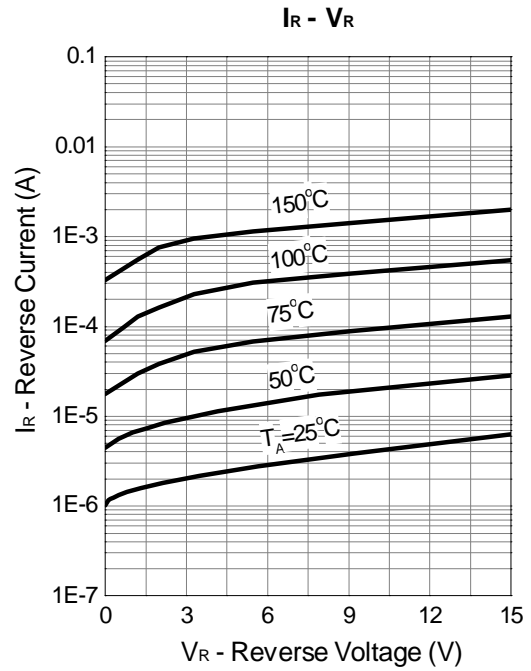
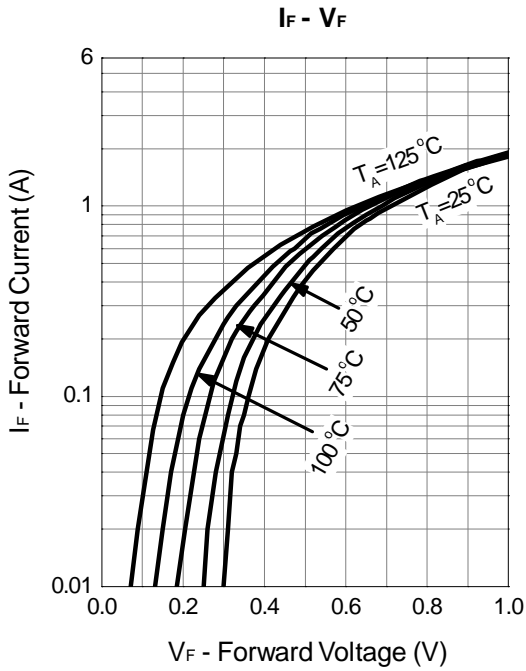
Gate Charge



Q_G - Gate Charge (nC)

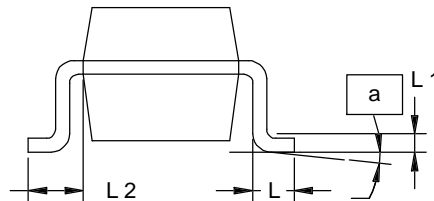
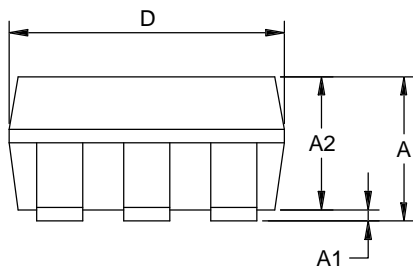
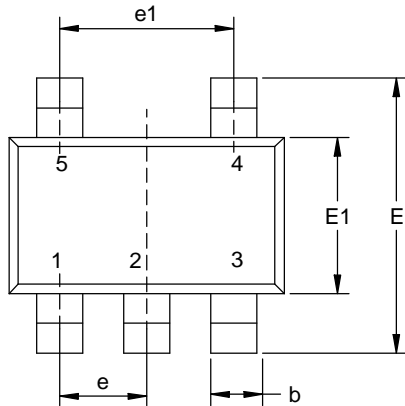
Typical Characteristics (Cont.)

SBD



Packaging Information

SOT-23-5

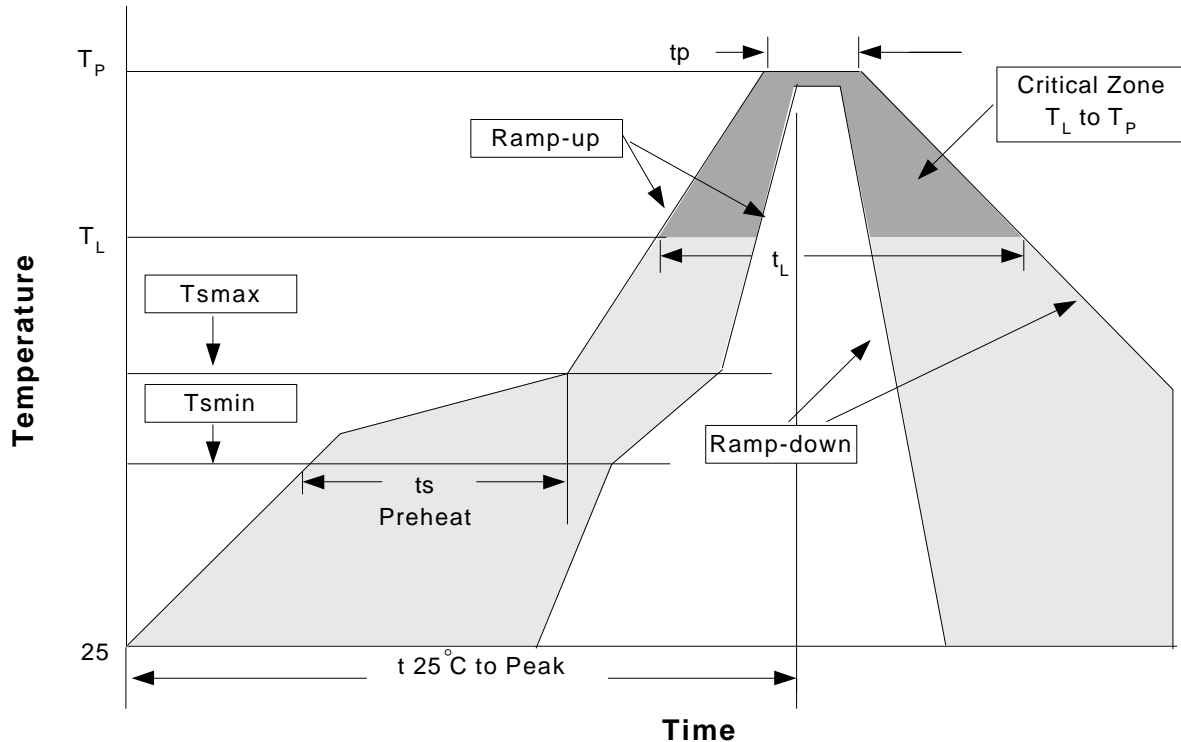


Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.95	1.45	0.037	0.057
A1	0.05	0.15	0.002	0.006
A2	0.90	1.30	0.035	0.051
b	0.30	0.50	0.011	0.019
D	2.8	3.00	0.110	0.118
E	2.6	3.00	0.102	0.118
E1	1.5	1.70	0.059	0.067
e	0.95BSC		0.037BSC	
e1	1.90BSC		0.074BSC	
L	0.35	0.55	0.014	0.022
L1	0.20 BSC		0.008 BSC	
L2	0.5	0.7	0.020	0.028
N	5		5	
α	0°	10°	0°	10°

Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb), 100%Sn
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.	3°C/second max.
Preheat <ul style="list-style-type: none"> - Temperature Min (T_{smin}) - Temperature Max (T_{smax}) - Time (min to max) (t_s) 	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: <ul style="list-style-type: none"> - Temperature (T_L) - Time (t_L) 	183°C 60-150 seconds	217°C 60-150 seconds
Peak/Classification Temperature (T_p)	See table 1	See table 2
Time within 5°C of actual Peak Temperature (t_p)	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Notes: All temperatures refer to topside of the package .Measured on the body surface.

Classification Reflow Profiles(Cont.)

Table 1. SnPb Eutectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

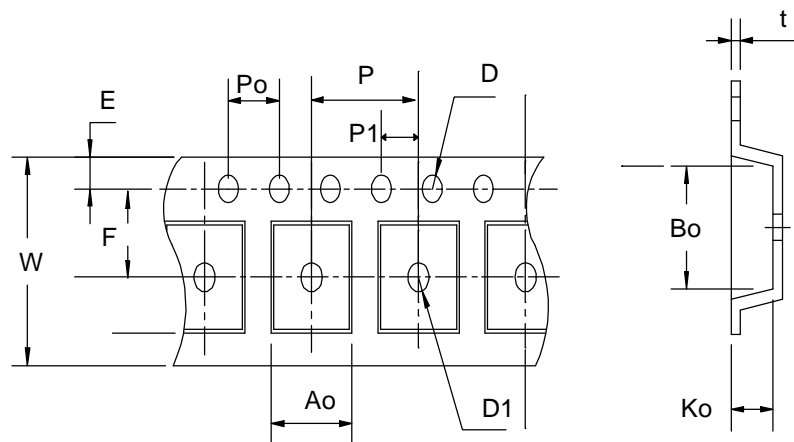
Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

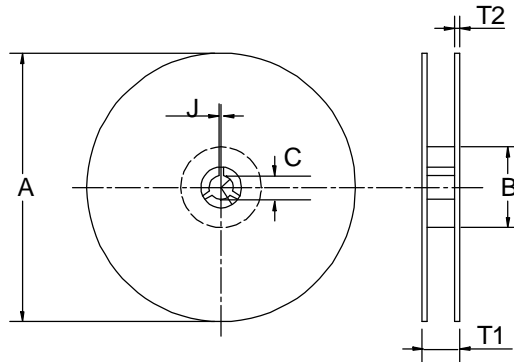
Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

Carrier Tape & Reel Dimensions



Carrier Tape & Reel Dimensions



Application	A	B	C	J	T1	T2	W	P	E
SOT-23-5	178±1	72 ± 1.0	13.0 + 0.2	2.5 ± 0.15	8.4 ± 2	1.5± 0.3	8.0+ ^{0.3} -0.3	4 ± 0.1	1.75± 0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	3.5 ± 0.05	1.5 +0.1	1.5 +0.1	4.0 ± 0.1	2.0 ± 0.1	3.15 ± 0.1	3.2± 0.1	1.4± 0.1	0.2±0.03

(mm)

Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
SOT-23-5	8	5.3	3000

Customer Service

Anpec Electronics Corp.

Head Office :

5F, No. 2 Li-Hsin Road, SBIP,

Hsin-Chu, Taiwan, R.O.C.

Tel : 886-3-5642000

Fax : 886-3-5642050

Taipei Branch :

7F, No. 137, Lane 235, Pac Chiao Rd.,

Hsin Tien City, Taipei Hsien, Taiwan, R. O. C.

Tel : 886-2-89191368

Fax : 886-2-89191369